ABSTRACT OF THE DISCLOSURE

The present invention is an input/output (I/O) structure for an integrated circuit device which increases the input signal energy transfer characteristic and allows for increased operating frequency of the device. The I/O structure includes a conductive region in a doped region below a semiconductor bond pad. The I/O structure also includes a tapped region coupled to a supply voltage. The I/O structure may also include an output driver transistor layout with a tapped source region to decrease a parasitic series resistance between a drain region and a source voltage.